

808 nm High-Power Laser Diode (AL808T1000)

Features:

Output power: 1w(CW)
Variety of stripe width
Efficient quantum well structure

Application:

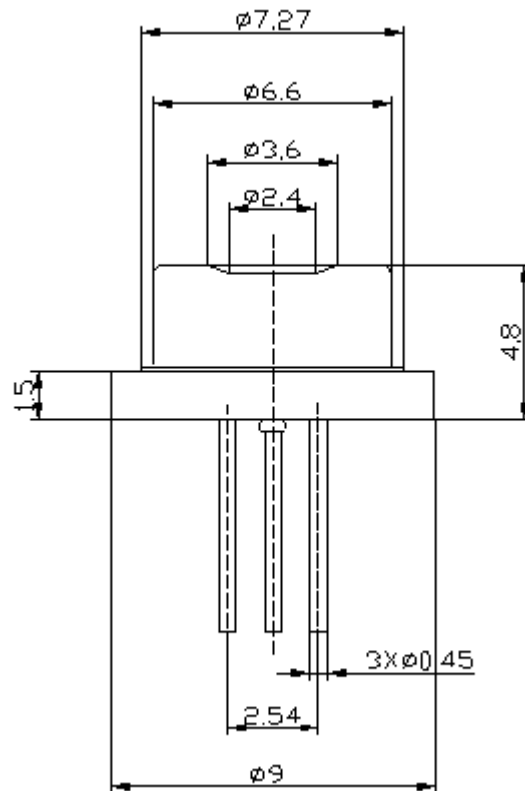
Solid-state laser pumping
Medical usage
Beacons and Illumination
Free-space communication
Infrared light sources



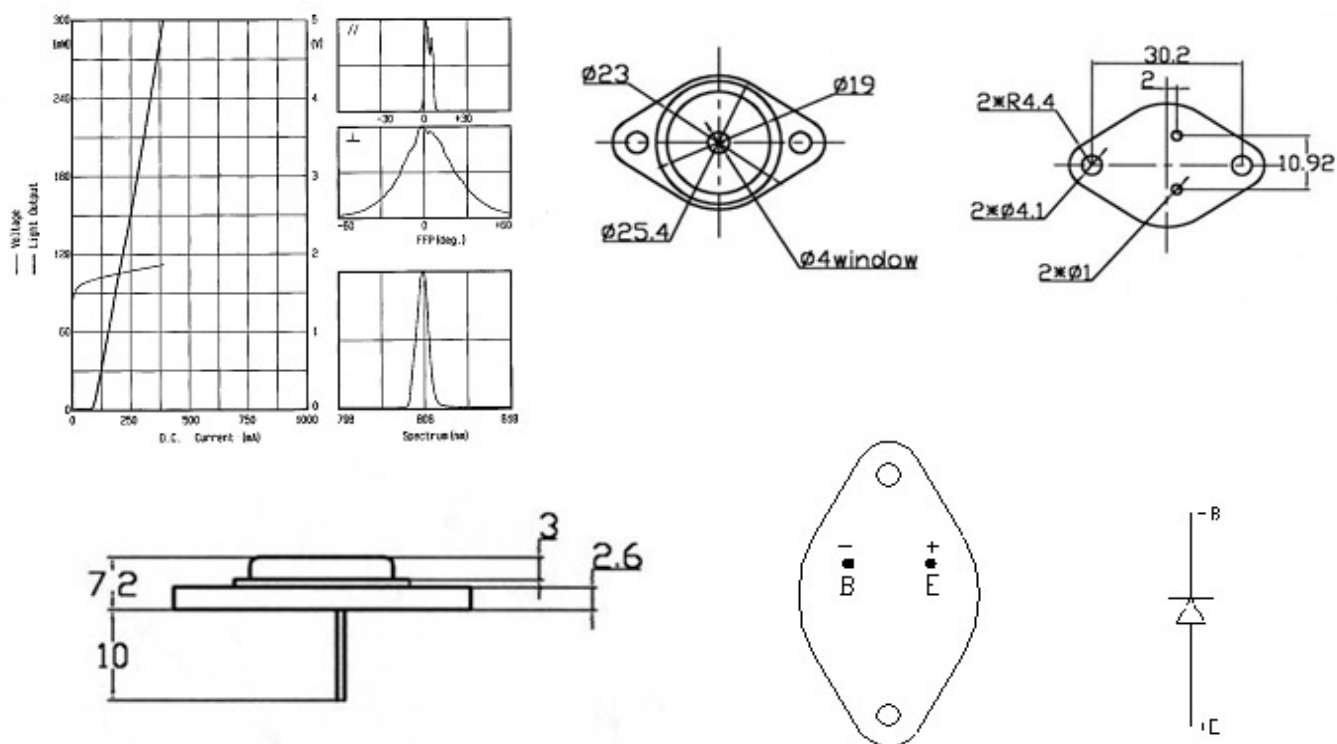
Specifications:

Parameter	Value
	AL808T1000
CW output power (mW)	1000
Peak wavelength (nm)	808 ± 5
Spectral width (nm)	≤ 5
Threshold current (A)	≤ 200
Operating current (mA)	≤ 1200
Operating voltage (V)	1.8~2.2
Slope efficiency (W/A)	≥ 0.9
Beam divergence $\theta_{\perp} \times \theta_{\parallel}$ (deg.)	12/40
Wavelength temperature coefficient (nm/°C)	0.3
Emitting area (μm)	100×1
Serial resistance (Ω)	≤ 1.5
Lifetime(h)	10000
Package	TO-5

TO-5 Package: (Unit: mm)



TO3 Packing



封装 C-block Heat Sink: (Unit : mm, Heat Sink(+))
C-block (C)

